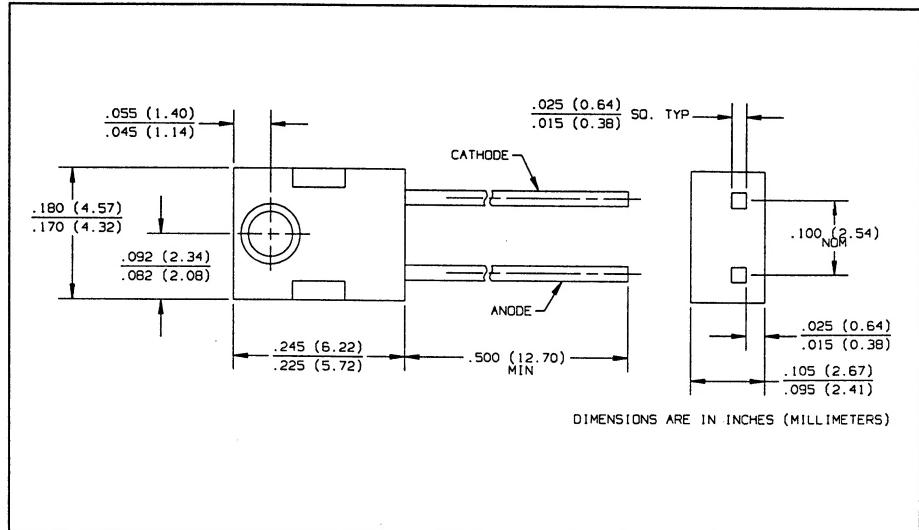
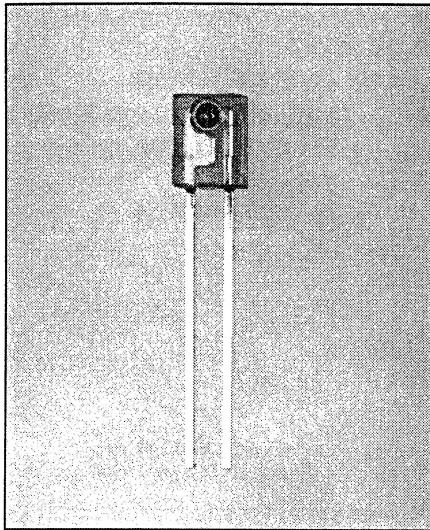


GaAlAs Plastic Infrared Emitting Diodes

Types OP245A, OP245B, OP245C, OP245D



Features

- Mechanically and spectrally matched to the OP555 and OP565 series devices
- Wavelength matched to silicon's peak response
- Significantly higher power output than GaAs at equivalent drive currents
- Side-looking package for space limited applications

Description

The OP245 series devices are 890 nm high intensity gallium aluminum arsenide infrared emitting diodes molded in IR transmissive amber tinted epoxy packages. The side-looking packages are for use in PC board mounted slotted switches or as easily mounted interrupt detectors.

Replaces

K6650

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

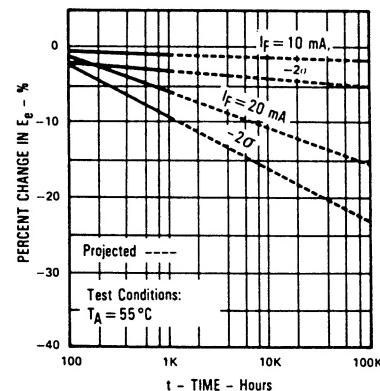
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μ s pulse width, 300 pps)	3.0 A
Storage and Operating Temperature Range	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	260° C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

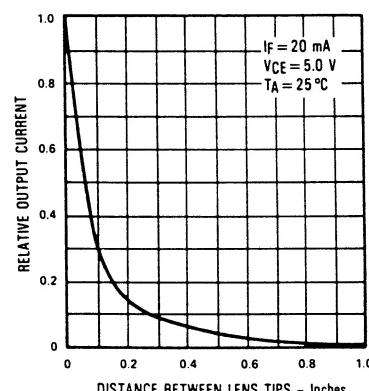
- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. A max. of 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly 1.33 mW/ $^\circ C$ above 25° C.
- (3) $E_e(APT)$ is a measurement of the average apertured radiant incidence upon a sensing area 0.180" (4.57 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.653" (16.6 mm) from the lens tip. $E_e(APT)$ is not necessarily uniform within the measured area.

Typical Performance Curves

Percent Changes in Radiant Intensity
vs Time



Coupling Characteristics
of OP245 and OP555



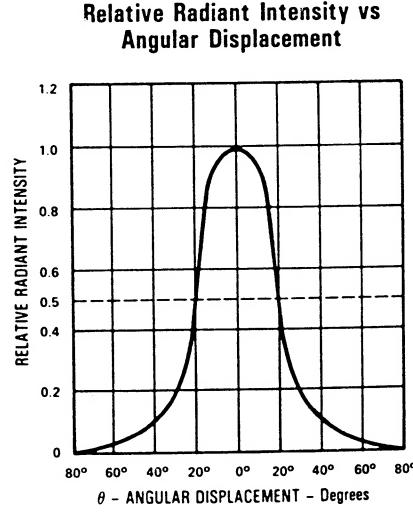
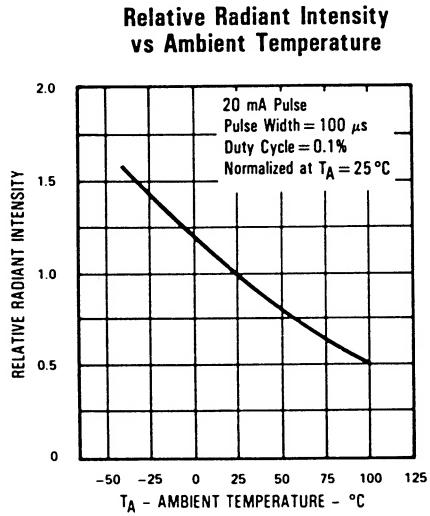
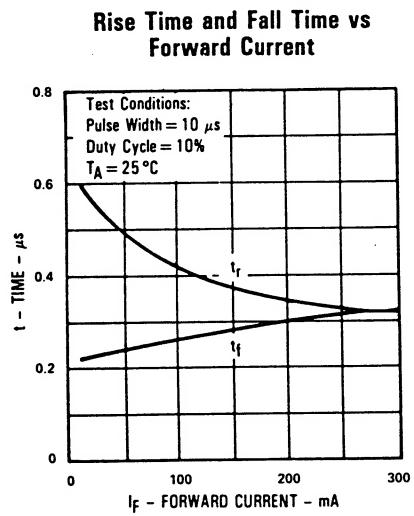
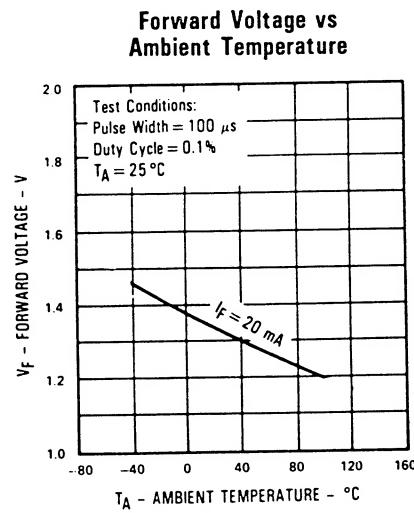
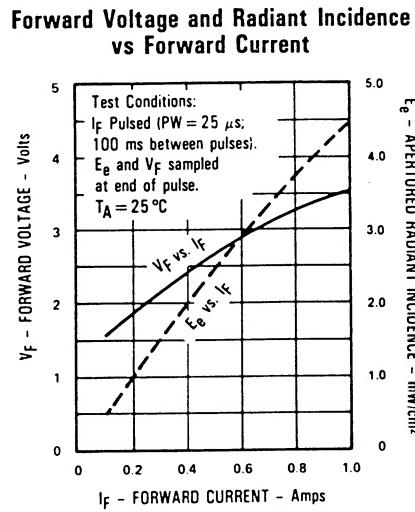
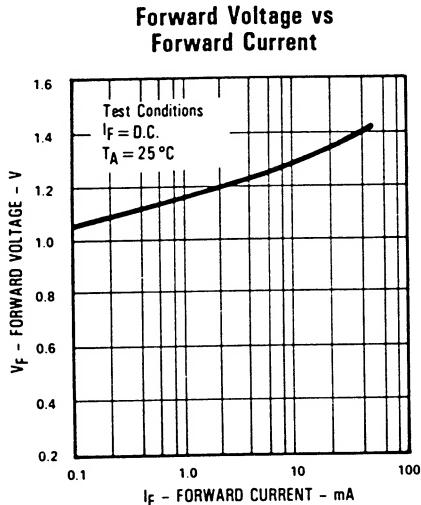
Types OP245A, OP245B, OP245C, OP245D

Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
$E_e(APT)$	Apertured Radiant Incidence	OP245D OP245C OP245B OP245A	0.05 0.20 0.40 0.60		0.86 1.20	mW/cm^2	$I_F = 20\text{ mA}^{(3)}$ $I_F = 20\text{ mA}^{(3)}$ $I_F = 20\text{ mA}^{(3)}$ $I_F = 20\text{ mA}^{(3)}$
V_F	Forward Voltage			1.80	V	$I_F = 20\text{ mA}$	
I_R	Reverse Current			100	μA	$V_R = 2\text{ V}$	
λ_p	Wavelength at Peak Emission			890	nm	$I_F = 10\text{ mA}$	
B	Spectral Bandwidth Between Half Power Points			80	nm	$I_F = 10\text{ mA}$	
$\Delta\lambda_p/\Delta T$	Spectral Shift with Temperature			+0.18	$nm/^\circ C$	$I_F = \text{Constant}$	
θ_{HP}	Emission Angle at Half Power Points			40	Deg.	$I_F = 20\text{ mA}$	
t_r	Output Rise Time			500	ns	$I_F(PK) = 100\text{ mA},$ $PW = 10\text{ }\mu\text{s, D.C.} = 10\%$	
t_f	Output Fall Time			250	ns		

INFRARED
EMITTING
DIODES

Typical Performance Curves



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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